Laurent Cerutti

List of Publications by Year
in descending order

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184 papers	3,106 citations	147566 31 h-index	197535 49 g-index
187 all docs	187 docs citations	187 times ranked	2708 citing authors

#	Article	IF	Citations
1	On the mechanisms of spontaneous growth of III-nitride nanocolumns by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2008, 310, 4035-4045.	0.7	165
2	Wurtzite GaN nanocolumns grown on Si(001) by molecular beam epitaxy. Applied Physics Letters, 2006, 88, 213114.	1.5	153
3	Growth, morphology, and structural properties of group-III-nitride nanocolumns and nanodisks. Physica Status Solidi (B): Basic Research, 2007, 244, 2816-2837.	0.7	148
4	Silicon-Based Photonic Integration Beyond the Telecommunication Wavelength Range. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 394-404.	1.9	106
5	MBE growth and characterization of type-II InAs/GaSb superlattices for mid-infrared detection. Journal of Crystal Growth, 2005, 274, 6-13.	0.7	91
6	Silicon-on-insulator spectrometers with integrated GaInAsSb photodiodes for wide-band spectroscopy from 1510 to 2300 nm. Optics Express, 2013, 21, 6101.	1.7	82
7	Continuous-wave operation above room temperature of GaSb-based laser diodes grown on Si. Applied Physics Letters, 2011, 99, .	1.5	78
8	GaSb-Based Laser, Monolithically Grown on Silicon Substrate, Emitting at 1.55 mum at Room Temperature. IEEE Photonics Technology Letters, 2010, 22, 553-555.	1.3	67
9	Single-frequency tunable Sb-based VCSELs emitting at 2.3 /spl mu/m. IEEE Photonics Technology Letters, 2005, 17, 2020-2022.	1.3	66
10	Silicon-based heterogeneous photonic integrated circuits for the mid-infrared. Optical Materials Express, 2013, 3, 1523.	1.6	65
11	Localized surface plasmon resonances in highly doped semiconductors nanostructures. Applied Physics Letters, 2012, 101, .	1.5	58
12	All-semiconductor plasmonic gratings for biosensing applications in the mid-infrared spectral range. Optics Express, 2016, 24, 16175.	1.7	57
13	Quantum cascade lasers grown on silicon. Scientific Reports, 2018, 8, 7206.	1.6	56
14	Brewster â€œmodeâ€•in highly doped semiconductor layers: an all-optical technique to monitor doping concentration. Optics Express, 2014, 22, 24294.	1.7	54
15	Study of evanescently-coupled and grating-assisted GaInAsSb photodiodes integrated on a silicon photonic chip. Optics Express, 2012, 20, 11665.	1.7	51
16	Metamorphic IIIâ€“V semiconductor lasers grown on silicon. MRS Bulletin, 2016, 41, 218-223.	1.7	47
17	High temperature continuous wave operation of Sb-based vertical external cavity surface emitting laser near 2.3Î¼m. Journal of Crystal Growth, 2004, 268, 128-134.	0.7	46
18	Free-Space Communication With Directly Modulated Mid-Infrared Quantum Cascade Devices. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-9.	1.9	46

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19	GaSbBi/GaSb quantum well laser diodes. Applied Physics Letters, 2017, 110, .	1.5	45
20	Universal description of III-V/Si epitaxial growth processes. Physical Review Materials, 2018, 2, .	0.9	43
21	Mid-infrared laser diodes epitaxially grown on on-axis (001) silicon. Optica, 2020, 7, 263.	4.8	42
22	Hyperbolic metamaterials and surface plasmon polaritons. Optica, 2017, 4, 1409.	4.8	41
23	GaSb-based, 2.2â€‚Î¼m type-I laser fabricated on GaAs substrate operating continuous wave at room temperature. Applied Physics Letters, 2009, 94, 023506.	1.5	40
24	Molecular beam epitaxy and characterization of high Bi content GaSbBi alloys. Journal of Crystal Growth, 2017, 477, 144-148.	0.7	39
25	Intracavity laser absorption spectroscopy with a vertical external cavity surface emitting laser at 2.3Î¼m: Application to water and carbon dioxide. Chemical Physics Letters, 2005, 416, 22-27.	1.2	38
26	Room-temperature operation of a 2.25â€‚Î¼m electrically pumped laser fabricated on a silicon substrate. Applied Physics Letters, 2009, 94, .	1.5	37
27	III-V-on-silicon integrated micro - spectrometer for the 3 Î¼m wavelength range. Optics Express, 2016, 24, 9465.	1.7	36
28	Room-temperature continuous-wave operation in the telecom wavelength range of GaSb-based lasers monolithically grown on Si. APL Photonics, 2017, 2, .	3.0	36
29	Heterogeneous Integration of GaInAsSb p-i-n Photodiodes on a Silicon-on-Insulator Waveguide Circuit. IEEE Photonics Technology Letters, 2011, 23, 1760-1762.	1.3	34
30	Mid-infrared GaSb-based EP-VCSEL emitting at 2.63â€…[micro sign]m. Electronics Letters, 2009, 45, 265.	0.5	33
31	Highly doped semiconductor plasmonic nanoantenna arrays for polarization selective broadband surface-enhanced infrared absorption spectroscopy of vanillin. Nanophotonics, 2017, 7, 507-516.	2.9	33
32	Distributed feedback GaSb based laser diodes with buried grating: a new field of single-frequency sources from 2 to 3 Âµm for gas sensing applications. Optics Express, 2015, 23, 19118.	1.7	32
33	X-ray diffraction study of GaSb grown by molecular beam epitaxy on silicon substrates. Journal of Crystal Growth, 2016, 439, 33-39.	0.7	32
34	Low threshold, room temperature laser diode pumped Sb-based VECSEL emitting around 2.1â€…[micro sign]m. Electronics Letters, 2003, 39, 290.	0.5	30
35	GaSb-based VCSELs emitting in the mid-infrared wavelength range (2â€“3Î¼m) grown by MBE. Journal of Crystal Growth, 2009, 311, 1912-1916.	0.7	29
36	Midwave infrared barrier detector based on Ga-free InAs/InAsSb type-II superlattice grown by molecular beam epitaxy on Si substrate. Infrared Physics and Technology, 2019, 96, 39-43.	1.3	29

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37	Surface-Enhanced Thermal Emission Spectroscopy with Perfect Absorber Metasurfaces. ACS Photonics, 2019, 6, 1506-1514.	3.2	28
38	Silicon surface preparation for III-V molecular beam epitaxy. Journal of Crystal Growth, 2015, 413, 17-24.	0.7	27
39	Heavily Doped Semiconductor Metamaterials for Midâ€Infrared Multispectral Perfect Absorption and Thermal Emission. Advanced Optical Materials, 2020, 8, 1901502.	3.6	27
40	Silicon-on-insulator shortwave infrared wavelength meter with integrated photodiodes for on-chip laser monitoring. Optics Express, 2014, 22, 27300.	1.7	26
41	Localized surface plasmon resonance frequency tuning in highly doped InAsSb/GaSb one-dimensional nanostructures. Nanotechnology, 2016, 27, 425201.	1.3	23
42	Zinc-blende group III-V/group IV epitaxy: Importance of the miscut. Physical Review Materials, 2020, 4, .	0.9	23
43	AlAsSb/GaSb doped distributed Bragg reflectors for electrically pumped VCSELs emitting around 2.3 Âµm. Semiconductor Science and Technology, 2007, 22, 1140-1144.	1.0	22
44	Single-Mode Monolithic GaSb Vertical-Cavity Surface-Emitting Laser. Optics Express, 2012, 20, 15540.	1.7	22
45	A Stressâ€Free and Textured GaP Template on Silicon for Solar Water Splitting. Advanced Functional Materials, 2018, 28, 1801585.	7.8	22
46	InAs-based quantum cascade lasers grown on on-axis (001) silicon substrate. APL Photonics, 2020, 5, .	3.0	22
47	2.36â€…[micro sign]m diode pumped VCSEL operating at room temperature in continuous wave with circular TEM00 output beam. Electronics Letters, 2004, 40, 869.	0.5	20
48	Room-Temperature Continuous-Wave Operation of 2.3-mum Sb-Based Electrically Pumped Monolithic Vertical-Cavity Lasers. IEEE Photonics Technology Letters, 2008, 20, 1745-1747.	1.3	20
49	Thermal Management for High-Power Single-Frequency Tunable Diode-Pumped VECSEL Emitting in the Near- and Mid-IR. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1701108-1701108.	1.9	20
50	Mid-infrared IIIâ€“V semiconductor lasers epitaxially grown on Si substrates. Light: Science and Applications, 2022, 11, .	7.7	20
51	2-2.7Î¼m single frequency tunable Sb-based lasers operating in CW at RT: microcavity and external cavity VCSELs, DFB. , 2006, , .		18
52	Distributed feedback GaSb based laser diodes with buried grating. Applied Physics Letters, 2014, 104, .	1.5	18
53	Anti phase boundary free GaSb layer grown on 300 mm (001)-Si substrate by metal organic chemical vapor deposition. Thin Solid Films, 2018, 645, 5-9.	0.8	18
54	Crystal Phase Control during Epitaxial Hybridization of IIIâ€V Semiconductors with Silicon. Advanced Electronic Materials, 2022, 8, 2100777.	2.6	18

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55	Technologies for thermal management of mid-IR Sb-based surface emitting lasers. Semiconductor Science and Technology, 2010, 25, 045021.	1.0	17
56	CRDS with a VECSEL for broad-band high sensitivity spectroscopy in the 2.3 Î¼m window. Review of Scientific Instruments, 2016, 87, 083109.	0.6	17
57	Extended Continuous Tuning of a Single-Frequency Diode-Pumped Vertical-External-Cavity Surface-Emitting Laser at 2.3 mum. IEEE Photonics Technology Letters, 2008, 20, 1947-1949.	1.3	16
58	Type I GaSb1-xBix/GaSb quantum wells dedicated for mid infrared laser applications: Photoreflectance studies of bandgap alignment. Journal of Applied Physics, 2019, 125, .	1.1	16
59	Vertical Cavity Surface Emitting Laser sources for gas detection. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 631-635.	0.8	15
60	InAs/GaSb short-period superlattice injection lasers operating in 2.5â€…[micro sign]mâ€“3.5â€…[micro sign]m mid-infrared wavelength range. Electronics Letters, 2007, 43, 1285.	0.5	15
61	Room-temperature, monolithic, electrically-pumped type-L quantum-well Sb-based VCSELs emitting at 2.3â€…[micro sign]m. Electronics Letters, 2008, 44, 203.	0.5	15
62	Mid-infrared characterization of refractive indices and propagation losses in GaSb/AlXGa1â^'XAsSb waveguides. Applied Physics Letters, 2015, 107, .	1.5	15
63	Characterization of antimonide based material grown by molecular epitaxy on vicinal silicon substrates via a low temperature AlSb nucleation layer. Journal of Crystal Growth, 2017, 477, 65-71.	0.7	15
64	Surface-enhanced infrared absorption with Si-doped InAsSb/GaSb nano-antennas. Optics Express, 2017, 25, 26651.	1.7	15
65	Mid-IR GaSb-Based Bipolar Cascade VCSELs. IEEE Photonics Technology Letters, 2013, 25, 882-884.	1.3	14
66	Low-loss orientation-patterned GaSb waveguides for mid-infrared parametric conversion. Optical Materials Express, 2017, 7, 3011.	1.6	14
67	Microstructure and interface analysis of emerging Ga(Sb,Bi) epilayers and Ga(Sb,Bi)/GaSb quantum wells for optoelectronic applications. Applied Physics Letters, 2018, 112, .	1.5	14
68	Interface energy analysis of IIIâ€“V islands on Si (001) in the Volmer-Weber growth mode. Applied Physics Letters, 2018, 113, .	1.5	14
69	Quantum well interband semiconductor lasers highly tolerant to dislocations. Optica, 2021, 8, 1397.	4.8	14
70	Fabrication and Characterization of GaSb-Based Monolithic Resonant-Cavity Light-Emitting Diodes Emitting Around 2.3 Î¼m and Including a Tunnel Junction. IEEE Journal of Selected Topics in Quantum Electronics, 2008, 14, 1014-1021.	1.9	13
71	Optical-Feedback Cavity-Enhanced Absorption Spectroscopy Using a Short-Cavity Vertical-External-Cavity Surface-Emitting Laser. IEEE Photonics Technology Letters, 2010, 22, 1607-1609.	1.3	13
72	Metal-insulator-metal antennas in the far-infrared range based on highly doped InAsSb. Applied Physics Letters, 2017, 111, .	1.5	13

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73	GaSb-based composite quantum wells for laser diodes operating in the telecom wavelength range near 1.55-Î¼m. Applied Physics Letters, 2015, 106, .	1.5	12
74	On the origin of threading dislocations during epitaxial growth of III-Sb on Si(001): A comprehensive transmission electron tomography and microscopy study. Acta Materialia, 2018, 143, 121-129.	3.8	12
75	Phosphonate monolayers on InAsSb and GaSb surfaces for mid-IR plasmonics. Applied Surface Science, 2018, 451, 241-249.	3.1	12
76	Oxide-confined mid-infrared VCSELs. Electronics Letters, 2012, 48, 1616-1618.	0.5	11
77	2.7-$mu{m m}$ Single-Frequency ${m TEM}_{00}$ Low-Threshold Sb-Based Diode-Pumped External-Cavity VCSEL. IEEE Photonics Technology Letters, 2012, 24, 246-248.	1.3	11
78	Oxide confinement and high contrast grating mirrors for Mid-infrared VCSELs. Optical Materials Express, 2013, 3, 1576.	1.6	11
79	Fano-like resonances sustained by Si doped InAsSb plasmonic resonators integrated in GaSb matrix. Optics Express, 2015, 23, 29423.	1.7	10
80	Spectroscopic Nanoimaging of All-Semiconductor Plasmonic Gratings Using Photoinduced Force and Scattering Type Nanoscopy. ACS Photonics, 2018, 5, 4352-4359.	3.2	10
81	Microfluidic surface-enhanced infrared spectroscopy with semiconductor plasmonics for the fingerprint region. Reaction Chemistry and Engineering, 2020, 5, 124-135.	1.9	10
82	Interband cascade Lasers with AlGaAsSb cladding layers emitting at 33â€…Âµm. Optics Express, 2019, 27, 31425.	1.7	10
83	Infrared spectral filter based on all-semiconductor guided-mode resonance. Optics Letters, 2019, 44, 3090.	1.7	10
84	Relative intensity noise and intrinsic properties of RF mounted interband cascade laser. Applied Physics Letters, 2021, 119, .	1.5	10
85	Electron tomography on III-Sb heterostructures on vicinal Si(001) substrates: Anti-phase boundaries as a sink for threading dislocations. Scripta Materialia, 2017, 132, 5-8.	2.6	9
86	GaSb-based laser diodes grown on MOCVD GaAs-on-Si templates. Optics Express, 2021, 29, 11268.	1.7	9
87	Etched-cavity GaSb laser diodes on a MOVPE GaSb-on-Si template. Optics Express, 2020, 28, 20785.	1.7	9
88	Selective lateral etching of InAs/GaSb tunnel junctions for mid-infrared photonics. Semiconductor Science and Technology, 2012, 27, 085011.	1.0	8
89	IIIâ€“V/Silicon Photonics for Short-Wave Infrared Spectroscopy. IEEE Journal of Quantum Electronics, 2012, 48, 292-298.	1.0	8
90	InAs/InAsSb superlattice structure tailored for detection of the full midwave infrared spectral domain. Proceedings of SPIE, 2017, , .	0.8	8

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91	Design and properties of high-power highly coherent single-frequency VECSEL emitting in the near- to mid-IR for photonic applications. Proceedings of SPIE, 2011, , .	0.8	7
92	Efficient lateral confinement by an oxide aperture in a mid-infrared GaSb-based vertical light-emitting source. Journal Physics D: Applied Physics, 2011, 44, 142001.	1.3	7
93	In situ determination of the growth conditions of GaSbBi alloys. Journal of Crystal Growth, 2018, 495, 9-13.	0.7	7
94	Giant Rabi splitting at the phonon line within all-semiconductor metallic-insulator-metallic antennas. Physical Review B, 2019, 100, .	1.1	7
95	Interband mid-infrared lasers. , 2020, , 91-130.		7
96	Hole-well antimonide laser diodes on GaSb operating near 2.93â€…[micro sign]m. Electronics Letters, 2006, 42, 1400.	0.5	6
97	MBE growth of mid-IR diode lasers based on InAs/GaSb/InSb short-period superlattice active zones. Journal of Crystal Growth, 2009, 311, 1905-1907.	0.7	6
98	GaSb-based integrated lasers and photodetectors on a Silicon-On-Insulator waveguide circuit for sensing applications in the shortwave infrared. , 2012, , .		6
99	Mid-IR GaSb-based monolithic vertical-cavity surface-emitting lasers. Journal Physics D: Applied Physics, 2013, 46, 495101.	1.3	6
100	Molecular-beam epitaxy of GaInSbBi alloys. Journal of Applied Physics, 2019, 126, .	1.1	6
101	Molecular-beam epitaxy of GaSb on 6Â°-offcut (0â€¯0â€¯1) Si using a GaAs nucleation layer. Journal of Crystal Growth, 2020, 529, 125299.	0.7	6
102	3.3 Âµm interband-cascade resonant-cavity light-emitting diode with narrow spectral emission linewidth. Semiconductor Science and Technology, 2020, 35, 125029.	1.0	6
103	GaSb-based monolithic EP-VCSEL emitting above 2.5â€…[micro sign]m. Electronics Letters, 2008, 44, 1357.	0.5	5
104	Broad continuous tunable range with single frequency Sb-based external-cavity VCSEL emitting in MIR. Electronics Letters, 2009, 45, 629.	0.5	5
105	Mid-IR lasing from highly tensile-strained, type II, GaInAs/GaSb quantum wells. Electronics Letters, 2009, 45, 1320.	0.5	5
106	Integrated thin-film GaSb-based Fabry-Perot lasers: towards a fully integrated spectrometer on a SOI waveguide circuit. , 2013, , .		5
107	Direct measurement of the effective infrared dielectric response of a highly doped semiconductor metamaterial. Nanotechnology, 2017, 28, 125701.	1.3	5
108	Pedestal formation of all-semiconductor gratings through GaSb oxidation for mid-IR plasmonics. Journal Physics D: Applied Physics, 2018, 51, 015104.	1.3	5

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109	Inelastic light scattering spectroscopy of semiconductor nitride nanocolumns. Physica Status Solidi (B): Basic Research, 2007, 244, 2838-2846.	0.7	4
110	Method for improving the electrical insulating properties of wet thermal oxide of AlAsSb on GaSb substrates. Applied Physics Letters, 2013, 103, .	1.5	4
111	Transmission electron microscopy of Ga(Sb, Bi)/GaSb quantum wells with varying Bi content and quantum well thickness. Semiconductor Science and Technology, 2018, 33, 094006.	1.0	4
112	Thermal performance of GaInSb quantum well lasers for silicon photonics applications. Applied Physics Letters, 2021, 118, .	1.5	4
113	Type-I quantum-well VCSEL structure on GaSb emitting in the 2â€“2.5 Î¼m range. IEE Proceedings: Optoelectronics, 2002, 149, 22-26.	0.8	3
114	Interfaces in GaxIn1âˆ’xAsySb1âˆ’yâˆ•AlxGa1âˆ’xAsySb1âˆ’y multi-quantum-well heterostructures probed by transmittance anisotropy spectroscopy. Journal of Applied Physics, 2005, 98, 066107.	1.1	3
115	Growth and characterization of GaInSb/GaInAsSb hole-well laser diodes emitting near 2.93Î¼m. Journal of Crystal Growth, 2007, 301-302, 967-970.	0.7	3
116	Heterogeneous GaSb/SOI mid-infrared photonic integrated circuits for spectroscopic applications. , 2011, , .		3
117	All-semiconductor plasmonics for mid-IR applications. , 2013, , .		3
118	GaSb-based all-semiconductor mid-IR plasmonics. , 2013, , .		3
119	Optical Detection and Spatial Modulation of Midâ€Infrared Surface Plasmon Polaritons in a Highly Doped Semiconductor. Advanced Optical Materials, 2018, 6, 1700492.	3.6	3
120	Mid-IR plasmonic compound with gallium oxide toplayer formed by GaSb oxidation in water. Semiconductor Science and Technology, 2018, 33, 095009.	1.0	3
121	The Interaction of Extended Defects as the Origin of Step Bunching in Epitaxial IIIâ€“V Layers on Vicinal Si(001) Substrates. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900290.	1.2	3
122	Optical properties and dynamics of excitons in Ga(Sb, Bi)/GaSb quantum wells: evidence for a regular alloy behavior. Semiconductor Science and Technology, 2020, 35, 025024.	1.0	3
123	Low threshold efficient Sb-based type-I quantum-well VCSEL emitting in the Î» = 2-2.5 Î¼m range. , 0, , .		2
124	Room temperature continuous wave operation of electrically-injected Sb-based RC-LED emitting near. Superlattices and Microstructures, 2008, 44, 62-69.	1.4	2
125	Mid-IR heterogeneous silicon photonics. Proceedings of SPIE, 2013, , .	0.8	2
126	Industrial integration of high coherence tunable VECSEL in the NIR and MIR. Proceedings of SPIE, 2014, , .	0.8	2

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127	Epitaxial Integration of Antimonide-Based Semiconductor Lasers on Si. Semiconductors and Semimetals, 2018, , 1-25.	0.4	2
128	GaSb Lasers Grown on Silicon Substrate for Telecom Applications. , 2018, , 625-635.		2
129	Plasmonic bio-sensing based on highly doped semiconductors. , 2017, , .		2
130	VCSELs Emitting in the 2â€“3 Âµm Wavelength Range. Springer Series in Optical Sciences, 2006, , 159-188.	0.5	2
131	Room temperature Sb-based mid-infrared VCSELs. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 1591-1596.	0.8	1
132	Integrated spectrometer and integrated detectors on Silicon-on-Insulator for short-wave infrared applications. , 2012, , .		1
133	2.7-Î¼m single-frequency TEM00 operation of Sb-based diode-pumped external-cavity VCSEL. , 2012, , .		1
134	Distributed-feedback GaSb-based laser diodes in the 2.3 to 3.3Î¼m wavelength range. Proceedings of SPIE, 2014, , .	0.8	1
135	First orientation-patterned GaSb ridge waveguides fabrication and preliminary characterization for frequency conversion in the mid-infrared. Proceedings of SPIE, 2016, , .	0.8	1
136	Industrial integration of high coherence tunable VECSEL in the NIR and MIR. , 2016, , .		1
137	Industrial integration of high coherence tunable single frequency semiconductor lasers based on VECSEL technology for scientific instrumentation in NIR and MIR. , 2017, , .		1
138	Hyperbolic metamaterials and surface plasmon polaritons: publisherâ€™s note. Optica, 2017, 4, 1558.	4.8	1
139	GaSbBi Alloys and Heterostructures: Fabrication and Properties. Springer Series in Materials Science, 2019, , 125-161.	0.4	1
140	Metamaterial perfect absorber based on heavily doped semiconductor for thermal emission. , 2019, , .		1
141	Semiconductor-based nanostructures for spectral filtering. , 2019, , .		1
142	Long-wave infrared spectral filter with semiconductor materials. , 2020, , .		1
143	Diode-pumped Sb-based VCSEL emitting between 2-2.5 Î¼m at RT in CW. , 0, , .		0
144	Continuous-wave operation at room temperature of diode-pumped antimony-based vcsel emitting above 2 Î¼m. , 0, , .		0

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145	Sb-based VCSEL operating at 2.3 Î¼m in continuous wave regime up to 350 K with a TEM00beam. European Physical Journal Special Topics, 2004, 119, 147-148.	0.2	0
146	<title>Continuous-wave operation up to 350K of optically-pumped antimony-based midinfrared VCSELs</title>. , 2004, , .		0
147	Single-frequency tunable VECSELs emitting at 2.3μm for spectroscopy application. , 0, , .		0
148	Gain, dichroÃ¯sm and quantum efficiency of Sb-based Quantum-Well VCSELs. , 2007, , .		0
149	Monolithic, Sb-based electrically pumped VCSELs emitting at 2.3Î¼m. , 2008, , .		0
150	GaSb-based microcavity EP-VCSEL emitting above 2.2 Î¼m in CW regime at RT. , 2008, , .		0
151	Room temperature, Sb-based monolithic EP-VCSEL at 2.3 μm including 2 n-type DBR. , 2008, , .		0
152	GaSb-based mid-IR electrically-pumped VCSELs covering the wavelength range from 2.3 to 2.7 µm. , 2009, , .		0
153	Sb-based laser sources grown by molecular beam epitaxy on silicon substrates. Proceedings of SPIE, 2010, , .	0.8	0
154	Optimized GaAs High Contrast Grating Design and Fabrication for Mid-infrared Application at 2.3 Âµm. , 2011, , .		0
155	High temperature continuous wave operation of Sb-based monolithic EP-VCSEL with Selectively Etched Tunnel-Junction Apertures. , 2012, , .		0
156	AlOx/GaAs high contrast grating mirrors for mid infrared VCSELs. , 2012, , .		0
157	GaSb-based laser monolithically grown on Si substrate by molecular beam epitaxy. , 2012, , .		0
158	GaSb-based laser monolithically grown on Si substrate operating under cw at room temperature. , 2012, , .		0
159	Long-wavelength silicon photonic integrated circuits. , 2014, , .		0
160	Technologies of oxide confinement and high contrast grating mirrors for mid-infrared VCSELs. , 2014, , .		0
161	Observation of Fano resonances in highly doped semiconductors plasmonic resonators (Presentation) Tj ETQq1 1 0.784314 rgBT /Ov	0.8	0
162	GaAs/AlOxhigh-contrast grating mirrors for mid-infrared VCSELs. , 2015, , .		0

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163	Parameter-tolerant design of high contrast gratings. , 2015, , .		0
164	THz absorbers with highly doped semiconductors based in plasmonic nano-resonators. , 2016, , .		0
165	Highly doped InAsSb plasmonic arrays for mid-infrared biosensing. , 2016, , .		0
166	GaSb lasers grown on Silicon substrate emitting in the telecom wavelength range. , 2016, , .		0
167	From 1-dimensional to 2-dimensional periodic semiconductor plasmonic resonators: Designing the optical response for sensing applications. , 2017, , .		0
168	Near-field Studies of Thermal Radiation and Local Density of States. , 2017, , .		0
169	Quantum cascade lasers grown on silicon. , 2018, , .		0
170	Toward MIR VCSELs operating in CW at RT. , 2019, , .		0
171	Progress in Interband Cascade Lasers: From Edge Emitting Lasers to VCSELs. , 2020, , .		0
172	Carrier recombination and temperature-dependence of GaInSb quantum well lasers for silicon photonics applications. , 2021, , .		0
173	Room temperature, continuous wave operation of an Sb-based laser grown on GaAs substrate. , 2009, , .		0
174	Demonstration of laser operation at room-temperature of an Sb-based mid-infrared multi-quantum-well structure monolithically grown on a Silicon substrate. , 2009, , .		0
175	Heterogeneously integrated InGaAsSb detectors on SOI waveguide circuits for short-wave infrared applications. , 2011, , .		0
176	Silicon-on-Insulator spectrometers with integrated GaInAsSb photodiode array for wideband operation from 1500 to 2300 nm.. , 2013, , .		0
177	M-lines characterization of the refractive index of GaSb and AlXGa1-XAsSb lattice-matched onto GaSb in the mid-infrared. , 2015, , .		0
178	Design and properties of high-power highly-coherent single-frequency VECSEL emitting in the near- to mid-IR for photonic applications. , 2017, , .		0
179	Industrial Low noise tunable integrated semiconductor laser: Dynamic instability and route to single frequency operation. , 2019, , .		0
180	Carrier Recombination Processes in 2.3-Âµm Epitaxially Grown Mid-Infrared Laser Diodes on Si(001). , 2021, , .		0

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181	Semiconductor nanostructures for spectral filtering. , 2020, , .		0
182	Semiconductor plasmonics and metamaterials for IR applications. , 2022, , .		0
183	Quantum plasmonics and hyperbolic material for biosensing. , 2022, , .		0
184	Impact of the ridge etchingâ€depth on GaSbâ€based laser diodes. Electronics Letters, 2022, 58, 162-163.	0.5	0